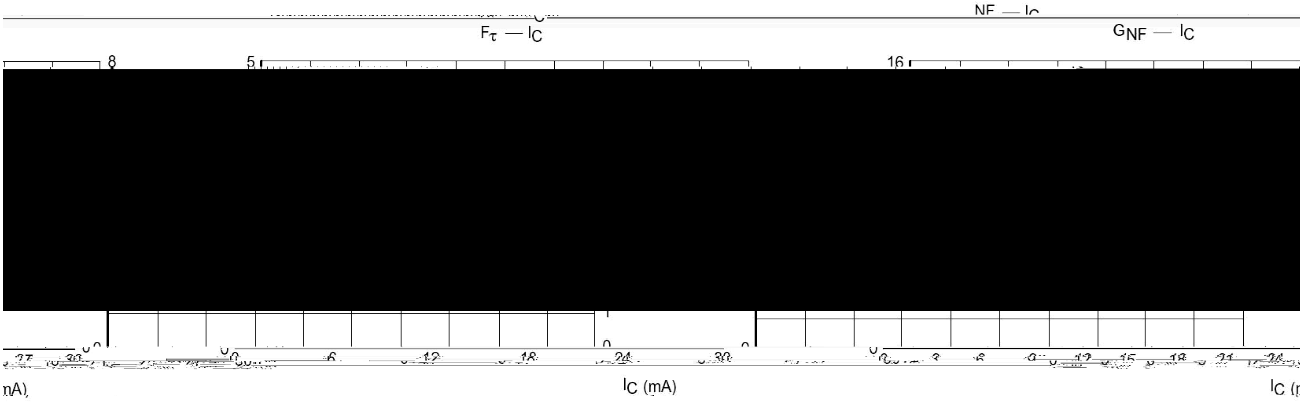
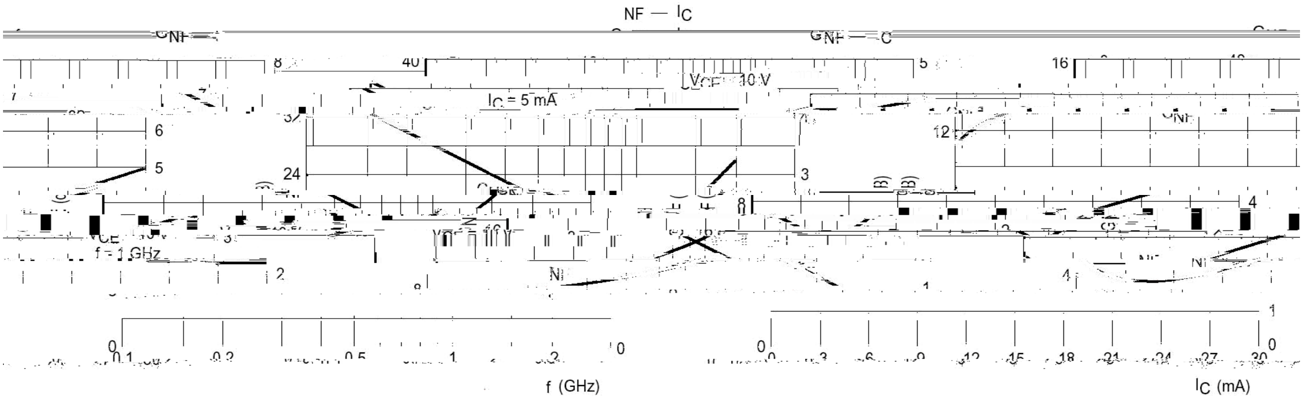
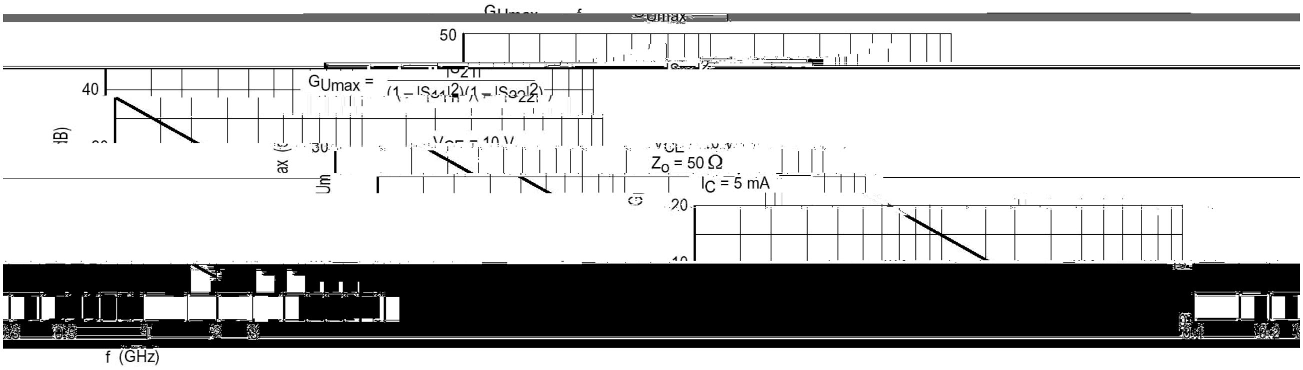
Silicon NPN transistor in a SOT-23 Plastic Package.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	25	V
Collector to Emitter Voltage	V_{CEO}	15	V
Emitter to Base Voltage	V_{EBO}	2	V
Collector Current	I_C	30	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	150	
Storage Temperature Range			

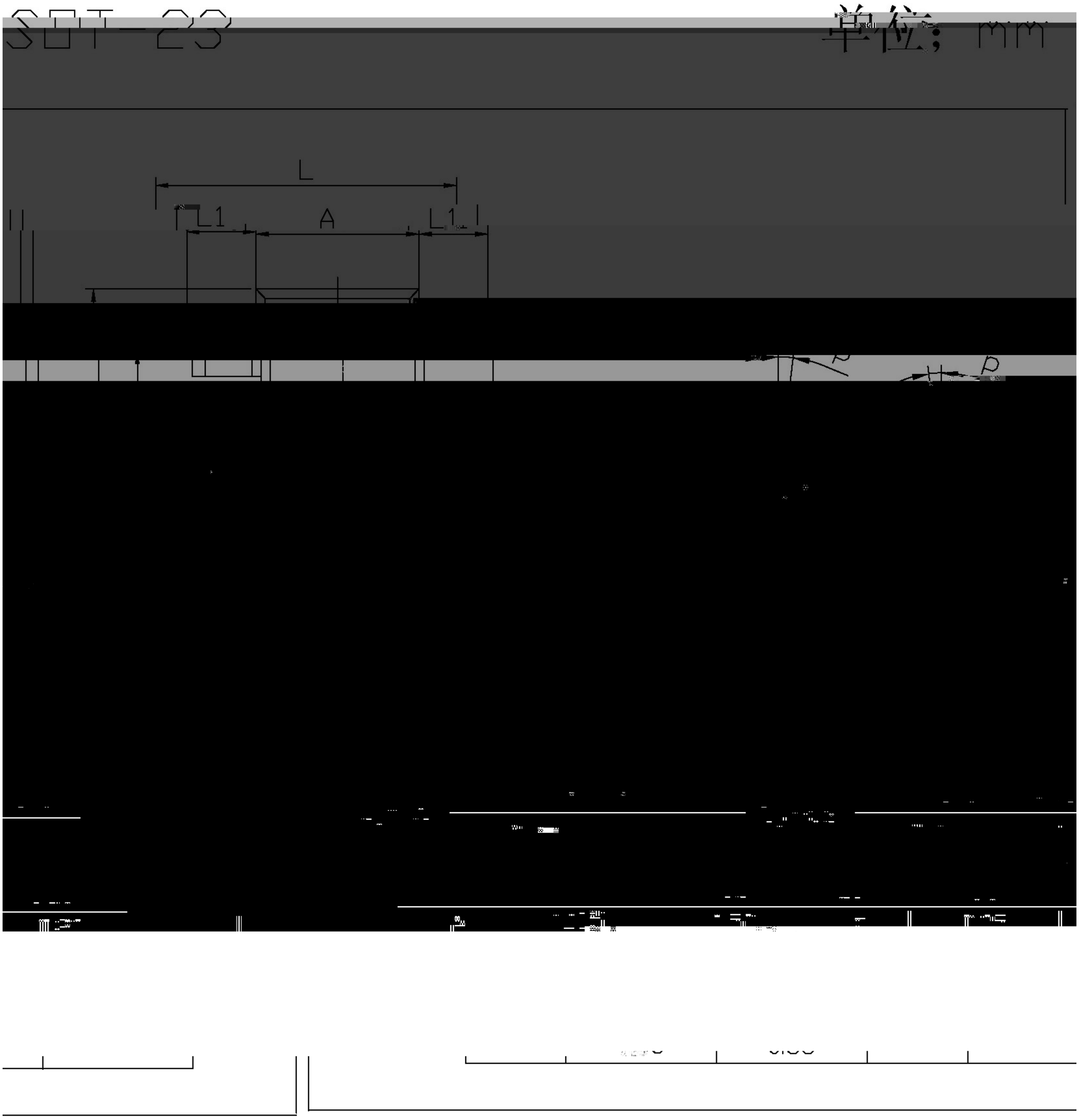
/ Electrical Characteristic Curve



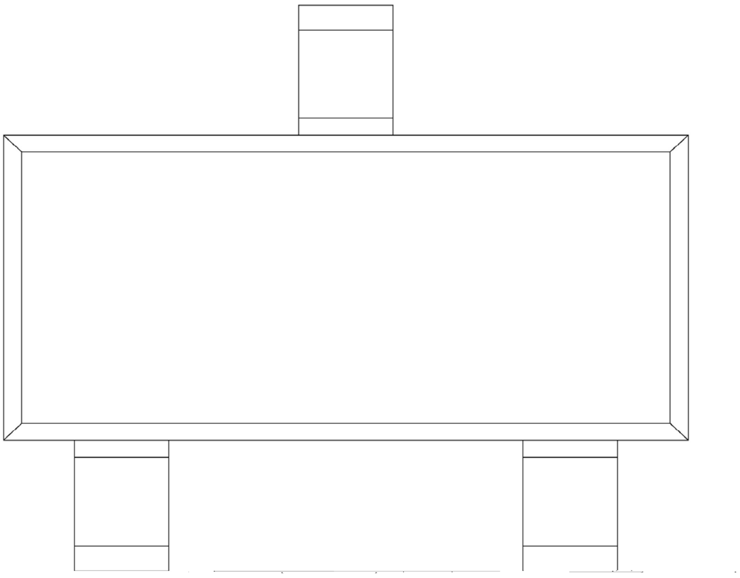




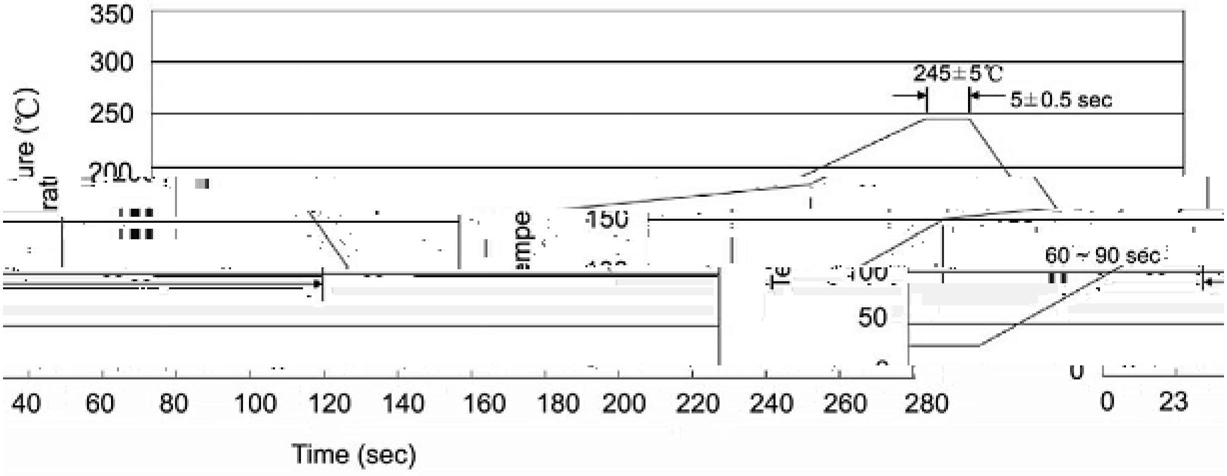
/ Package Dimensions



/ Marking Instructions



( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

1 25 150 60 90sec; 1.Preheating:25~150 , Time:60~90sec.

2 245 5 5 0.5sec; 2.Peak Temp.:245 5 , Duration:5 0.5sec.

3 2 10 /sec. 3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260 5 10 1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-23	3,000	10	30,000	6	180,000	7 ×8	180×120×180	390×385×205